

Zakhar D Kovalyuk

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226
ext. papers

3,747
ext. citations

2.8
avg, IF

4.88
L-index

#	Paper	IF	Citations
212	High electron mobility, quantum Hall effect and anomalous optical response in atomically thin InSe. <i>Nature Nanotechnology</i> , 2017 , 12, 223-227	28.7	723
211	Tuning the bandgap of exfoliated InSe nanosheets by quantum confinement. <i>Advanced Materials</i> , 2013 , 25, 5714-8	24	419
210	High broad-band photoresponsivity of mechanically formed InSe-graphene van der Waals heterostructures. <i>Advanced Materials</i> , 2015 , 27, 3760-6	24	252
209	The direct-to-indirect band gap crossover in two-dimensional van der Waals Indium Selenide crystals. <i>Scientific Reports</i> , 2016 , 6, 39619	4.9	114
208	Quantum confinement and photoresponsivity of In_2Se_3 nanosheets grown by physical vapour transport. <i>2D Materials</i> , 2016 , 3, 025030	5.9	68
207	Design of van der Waals interfaces for broad-spectrum optoelectronics. <i>Nature Materials</i> , 2020 , 19, 299-304	30.4	64
206	Engineering p-n junctions and bandgap tuning of InSe nanolayers by controlled oxidation. <i>2D Materials</i> , 2017 , 4, 025043	5.9	63
205	Room Temperature Electroluminescence from Mechanically Formed van der Waals III-VI Homojunctions and Heterojunctions. <i>Advanced Optical Materials</i> , 2014 , 2, 1064-1069	8.1	61
204	Electronic band structure of GaSe(0001): Angle-resolved photoemission and ab initio theory. <i>Physical Review B</i> , 2003 , 68,	3.3	55
203	Epitaxial growth of InSe and SnSe and In_2Se_3 on GaSe . <i>2D Materials</i> , 2018 , 5, 035026	5.9	55
202	Quantum confined acceptors and donors in InSe nanosheets. <i>Applied Physics Letters</i> , 2014 , 105, 221909	3.4	53
201	Interlayer Band-to-Band Tunneling and Negative Differential Resistance in van der Waals BP/InSe Field-Effect Transistors. <i>Advanced Functional Materials</i> , 2020 , 30, 1910713	15.6	41
200	Electrical and photoelectrical properties of photosensitive heterojunctions n-TiO ₂ /p-CdTe. <i>Semiconductor Science and Technology</i> , 2011 , 26, 125006	1.8	39
199	Giant Quantum Hall Plateau in Graphene Coupled to an InSe van der Waals Crystal. <i>Physical Review Letters</i> , 2017 , 119, 157701	7.4	33
198	Gate-Defined Quantum Confinement in InSe-Based van der Waals Heterostructures. <i>Nano Letters</i> , 2018 , 18, 3950-3955	11.5	33
197	Mechanisms of charge transport in anisotype n-TiO ₂ /p-CdTe heterojunctions. <i>Semiconductors</i> , 2011 , 45, 1077-1081	0.7	28
196	Two-Dimensional Covalent Crystals by Chemical Conversion of Thin van der Waals Materials. <i>Nano Letters</i> , 2019 , 19, 6475-6481	11.5	26

195	Intrinsic conductive oxide p-InSe solar cells. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004 , 109, 252-255	3.1	26
194	Biexciton formation and exciton coherent coupling in layered GaSe. <i>Journal of Chemical Physics</i> , 2015 , 142, 212422	3.9	24
193	Formation and Healing of Defects in Atomically Thin GaSe and InSe. <i>ACS Nano</i> , 2019 , 13, 5112-5123	16.7	23
192	Mechanism of excitonic dephasing in layered InSe crystals. <i>Physical Review B</i> , 2014 , 89,	3.3	22
191	Formation of nanostructure on the surface of layered InSe semiconductor caused by oxidation under heating. <i>Physics of the Solid State</i> , 2007 , 49, 1572-1578	0.8	22
190	Native oxide emerging of the cleavage surface of gallium selenide due to prolonged storage. <i>Semiconductors</i> , 2008 , 42, 414-421	0.7	21
189	Light-dependent IV characteristics of TiO ₂ /CdTe heterojunction solar cells. <i>Semiconductor Science and Technology</i> , 2012 , 27, 055008	1.8	20
188	Coherent acoustic phonons in van der Waals nanolayers and heterostructures. <i>Physical Review B</i> , 2018 , 98,	3.3	19
187	Optical constants and polarimetric properties of ZnMnO ₂ thin films. <i>Optical Materials</i> , 2012 , 34, 1940-1945	4.3	18
186	Graphitic carbon/n-CdTe Schottky-type heterojunction solar cells prepared by electron-beam evaporation. <i>Solar Energy</i> , 2015 , 112, 78-84	6.8	17
185	Optical properties of TiO ₂ -MnO ₂ thin films prepared by electron-beam evaporation. <i>Technical Physics</i> , 2012 , 57, 1148-1151	0.5	17
184	Two-Dimensional Character of Electron Gas in Layered InSe Crystals. <i>Physica Status Solidi (B): Basic Research</i> , 1990 , 162, 213-225	1.3	17
183	Transport properties of sodium intercalated indium selenide. <i>Physica Status Solidi A</i> , 1987 , 104, K41-K45		16
182	High-Frequency Elastic Coupling at the Interface of van der Waals Nanolayers Imaged by Picosecond Ultrasonics. <i>ACS Nano</i> , 2019 , 13, 11530-11537	16.7	15
181	Electrical properties of anisotype heterojunctions n-CdZnO/p-CdTe. <i>Semiconductors</i> , 2012 , 46, 1152-1157	0.7	15
180	Self-organization of PbTe and SnTe nanostructures on the van der Walls GaSe(0001) surface. <i>Technical Physics Letters</i> , 2007 , 33, 86-90	0.7	15
179	Magnetic properties and surface morphology of layered In ₂ Se ₃ crystals intercalated with cobalt. <i>Physics of the Solid State</i> , 2013 , 55, 1148-1155	0.8	14
178	Resonant tunnelling into the two-dimensional subbands of InSe layers. <i>Communications Physics</i> , 2020 , 3,	5.4	13

177	Nanomechanical probing of the layer/substrate interface of an exfoliated InSe sheet on sapphire. <i>Scientific Reports</i> , 2016 , 6, 26970	4.9	13
176	Anomalies of magnetic properties of layered crystals InSe containing Mn. <i>Materials Science and Engineering C</i> , 2007 , 27, 1052-1055	8.3	13
175	Surface topology of GaSe oxidized crystals. <i>Superlattices and Microstructures</i> , 2008 , 44, 416-419	2.8	13
174	Ferromagnetic states in the In _{1-x} MnxSe layered crystal. <i>Physical Review B</i> , 2005 , 71,	3.3	13
173	Effect of gamma radiation on the properties of InSe photodiodes. <i>Technical Physics Letters</i> , 2005 , 31, 359-360	0.7	13
172	Polarisation-sensitive photodiode for the 632.8 nm spectral region. <i>Electronics Letters</i> , 1990 , 26, 664-664	1.1	13
171	Emission of free and bound excitons in layered gase crystals. <i>Physica Status Solidi (B): Basic Research</i> , 1983 , 117, 283-287	1.3	13
170	Photoquantum Hall Effect and Light-Induced Charge Transfer at the Interface of Graphene/InSe Heterostructures. <i>Advanced Functional Materials</i> , 2019 , 29, 1805491	15.6	13
169	2D nanocomposite photoconductive sensors fully dry drawn on regular paper. <i>Nanotechnology</i> , 2015 , 26, 255501	3.4	12
168	Ferromagnetism of layered GaSe semiconductors intercalated with cobalt. <i>Semiconductors</i> , 2012 , 46, 971-974	0.7	12
167	On some physical properties of InSe and GaSe semiconducting crystals intercalated by ferroelectrics. <i>Journal of Physics Condensed Matter</i> , 1997 , 9, L191-L195	1.8	12
166	Influence of Ni Impurity on the Absorption Spectrum of Layered GaSe Crystals. <i>Physica Status Solidi (B): Basic Research</i> , 1981 , 106, 621-626	1.3	12
165	Improved performance of InSe field-effect transistors by channel encapsulation. <i>Semiconductor Science and Technology</i> , 2018 , 33, 06LT01	1.8	11
164	Electrical properties of In ₂ Se ₃ layered crystals doped with cadmium, iodine, or copper. <i>Inorganic Materials</i> , 2007 , 43, 1271-1274	0.9	11
163	On the mechanisms of current transfer in n-In ₂ Se ₃ -p-GaSe heterostructures. <i>Technical Physics Letters</i> , 2002 , 28, 707-710	0.7	11
162	Enhanced Optical Emission from 2D InSe Bent onto Si-Pillars. <i>Advanced Optical Materials</i> , 2020 , 8, 2000888	2.8	10
161	Schottky-barrier thin-film transistors based on HfO ₂ -capped InSe. <i>Applied Physics Letters</i> , 2019 , 115, 033502	3.4	10
160	NMR study of the charge-density-wave state in VSe ₂ . <i>Physica Status Solidi (B): Basic Research</i> , 1983 , 119, 401-410	1.3	10

159	Large Tunneling Magnetoresistance in van der Waals Ferromagnet/Semiconductor Heterojunctions. <i>Advanced Materials</i> , 2021 , e2104658	24	10
158	Van der Waals SnSe ₂ (1-x)S _{2x} Alloys: Composition-Dependent Bowing Coefficient and Electron-Phonon Interaction. <i>Advanced Functional Materials</i> , 2020 , 30, 1908092	15.6	10
157	Graphene-InSe-graphene van der Waals heterostructures. <i>Journal of Physics: Conference Series</i> , 2015 , 647, 012001	0.3	9
156	The formation of organic (propolis films)/inorganic (layered crystals) interfaces for optoelectronic applications. <i>Superlattices and Microstructures</i> , 2008 , 44, 563-570	2.8	9
155	Properties of Hydrogenated GaSe Crystals. <i>Inorganic Materials</i> , 2005 , 41, 793-795	0.9	9
154	Photoresponse spectral investigations for anisotropic semiconductor InSe. <i>Optical Materials</i> , 2001 , 17, 279-281	3.3	9
153	Space-Charge Region Scattering in Indium Monoselenide. <i>Physica Status Solidi A</i> , 2000 , 180, 523-531		9
152	Annealing effect on conductivity anisotropy in indium selenide single crystals. <i>Physica Status Solidi A</i> , 1996 , 155, 451-460		9
151	Highly-mismatched InAs/InSe heterojunction diodes. <i>Applied Physics Letters</i> , 2016 , 109, 182115	3.4	9
150	APPLICATION OF LAYERED InSe AND GaSe CRYSTALS AND POWDERS FOR SOLID STATE HYDROGEN STORAGE 2007 , 325-340		9
149	The Interaction of Hydrogen with the van der Waals Crystal -InSe. <i>Molecules</i> , 2020 , 25,	4.8	8
148	Surface Barrier heterojunctions TiO ₂ /CdZnTe. <i>Semiconductor Science and Technology</i> , 2013 , 28, 015014	1.8	8
147	Temperature dependent electrical properties and barrier parameters of photosensitive heterojunctions n-Ti/p-Cd _{1-x} Zn _x Te. <i>Semiconductor Science and Technology</i> , 2015 , 30, 075006	1.8	8
146	Structural and optical characterization of the propolis films. <i>Applied Surface Science</i> , 2006 , 253, 279-282	6.7	8
145	Variation in the built-in potential of a photodiode based on an n-InSe-p-GaSe heterojunction in the course of aging. <i>Semiconductors</i> , 2004 , 38, 546-549	0.7	8
144	Influence of Intercalation by Metallic Atoms on the Shubnikov -de Haas Effect and the Energy Spectrum of Bi ₂ Te ₃ . <i>Physica Status Solidi (B): Basic Research</i> , 1992 , 169, 157-162	1.3	8
143	Crystal growth and elastic properties of In ₂ Se ₃ . <i>Inorganic Materials</i> , 2011 , 47, 1174-1177	0.9	7
142	Optical and photoelectric properties of barium-intercalated InSe and GaSe. <i>Inorganic Materials</i> , 2009 , 45, 1222-1225	0.9	7

141	Electrical properties of hybrid (ferromagnetic metal)/layered semiconductor Ni/p-GaSe structures. <i>Semiconductors</i> , 2010 , 44, 171-183	0.7	7
140	Age-induced oxide on cleaved surface of layered GaSe single crystals. <i>Applied Surface Science</i> , 2008 , 254, 2067-2071	6.7	7
139	Electrical and photoelectric characteristics of structures based on InSe and GaSe layered semiconductors irradiated with 12.5-MeV electrons. <i>Semiconductors</i> , 2008 , 42, 1292-1297	0.7	7
138	Weak ferromagnetism in InSe:Mn layered crystals. <i>Semiconductors</i> , 2005 , 39, 772-776	0.7	7
137	Heat capacity of the n-InSe single crystal layered semiconductor. <i>Journal of Applied Physics</i> , 2002 , 92, 5110-5112	2.5	7
136	Photoluminescence dynamics in few-layer InSe. <i>Physical Review Materials</i> , 2020 , 4,	3.2	7
135	Magnetotransport and lateral confinement in an InSe van der Waals Heterostructure. <i>2D Materials</i> , 2018 , 5, 035040	5.9	6
134	Structure of oxidized and unoxidized end faces of GaSe layered crystals. <i>Inorganic Materials</i> , 2014 , 50, 339-343	0.9	6
133	Effect of low-temperature annealing on the quality of InSe layered single crystals and the characteristics of n-InSe/p-InSe heterojunctions. <i>Semiconductors</i> , 2014 , 48, 545-550	0.7	6
132	On the Possibility of Layered Crystals Application for Solid State Hydrogen Storages - InSe and GaSe Crystals 2012 ,		6
131	Fabrication and Characterization of Photosensitive n-CdO/p-InSe Heterojunctions. <i>Acta Physica Polonica A</i> , 2013 , 124, 720-723	0.6	6
130	Carrier transport in layered semiconductor (p-GaSe)-ferroelectric (KNO ₃) composite nanostructures. <i>Semiconductors</i> , 2011 , 45, 338-349	0.7	6
129	Surface structure of unoxidized and oxidized Bi ₂ Se ₃ crystals. <i>Inorganic Materials</i> , 2010 , 46, 1296-1298	0.9	6
128	β -Radiation influence on the photoelectrical properties of oxide β -InSe heterostructure. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005 , 118, 147-149	3.1	6
127	Spectroscopic studies of 2H-PbI ₂ (Mn) layered crystals. <i>Physica Status Solidi (B): Basic Research</i> , 2005 , 242, 2427-2432	1.3	6
126	The injection peculiarities of minority charge carriers in the anisotype SIS structure. <i>Physica Status Solidi A</i> , 1989 , 115, K35-K37		6
125	Sodium Intercalation into Indium and Gallium Selenides. <i>Physica Status Solidi A</i> , 1987 , 102, K1-K5		6
124	Photosensitive anisotype n-ZnSe/p-InSe and n-ZnSe/p-GaSe heterojunctions. <i>Technical Physics</i> , 2014 , 59, 1205-1208	0.5	5

123	Influence of external factors on the self-organization of lead and tin telluride nanostructures on the BaF ₂ (111) surface under conditions close to the thermodynamic equilibrium. <i>Physics of the Solid State</i> , 2013 , 55, 181-195	0.8	5
122	Surface morphology and electrical resistance of the oxide film on InSe. <i>Inorganic Materials</i> , 2011 , 47, 749-752	0.9	5
121	Effect of the buffer layer of GaSe intrinsic oxide with nanometer thickness on electrical, photoelectric, and emissive properties of ITO-GaSe heterostructures. <i>Semiconductors</i> , 2007 , 41, 301-306	0.7	5
120	The effect of neutron radiation on the photoelectric parameters of ITO-GaSe structures. <i>Semiconductors</i> , 2007 , 41, 550-554	0.7	5
119	Effect of neutron radiation on the photoelectric parameters of p-n-InSe structures. <i>Technical Physics Letters</i> , 2007 , 33, 767-770	0.7	5
118	Oxide-p-InSe heterostructures with improved photoelectric characteristics. <i>Semiconductors</i> , 2004 , 38, 402-405	0.7	5
117	Energy band diagram of a photosensitive Sn-p-InSe structure. <i>Technical Physics Letters</i> , 2003 , 29, 480-484	0.7	5
116	p-GaSe-n-recrystallized InSe heterojunctions. <i>Technical Physics Letters</i> , 2000 , 26, 54-55	0.7	5
115	Influence of self-oxide formation regimes on the properties of oxide-p-InSe heterojunctions. <i>Technical Physics Letters</i> , 1999 , 25, 520-521	0.7	5
114	N-shaped volt-ampere characteristics of InSe single crystals at low temperatures. <i>Solid State Communications</i> , 1990 , 75, 465-467	1.6	5
113	Room Temperature Uniaxial Magnetic Anisotropy Induced By Fe-Islands in the InSe Semiconductor Van Der Waals Crystal. <i>Advanced Science</i> , 2018 , 5, 1800257	13.6	5
112	Nanocomposite structures grown by inserting ionic salt RbNO ₃ into van der Waals gaps of III-VI compound layered semiconductors. <i>Solid State Ionics</i> , 2015 , 273, 59-65	3.3	4
111	Spectral anisotropy of a photoresponse from heterojunctions based on GaSe and InSe layered crystals. <i>Technical Physics</i> , 2014 , 59, 407-410	0.5	4
110	Electrical properties of In ₂ Se ₃ <Mn> and InSe<Mn> crystals. <i>Inorganic Materials</i> , 2012 , 48, 103-105	0.9	4
109	Radiation resistance of photodiodes based on indium monoselenides under β radiation. <i>Journal of Nuclear Materials</i> , 2009 , 385, 489-494	3.3	4
108	Neutron diffraction studies of the negative thermal expansion in a layered indium selenide crystal. <i>Physics of the Solid State</i> , 2009 , 51, 2342-2346	0.8	4
107	Intrinsic transport properties of InSe studied by millimeter and submillimeter spectroscopy. <i>Solid State Communications</i> , 1998 , 105, 433-438	1.6	4
106	The effect of photocurrent amplification in an In ₂ O ₃ -GaSe heterostructure. <i>Technical Physics Letters</i> , 2001 , 27, 755-757	0.7	4

105	Effect of Laser Irradiation on Low-Temperature Photoconductivity and Photoluminescence Spectra of Gallium Selenide. <i>Physica Status Solidi (B): Basic Research</i> , 1989 , 153, 667-673	1.3	4
104	Alkali-Metal-Intercalated Indium and Gallium Selenides Non-Monotonous Shift of Exciton Lines. <i>Physica Status Solidi (B): Basic Research</i> , 1989 , 155, 717-722	1.3	4
103	Optical Properties of GaSe Crystals Containing Mn Impurity Atoms. I. Exciton-Phonon Interaction. <i>Physica Status Solidi (B): Basic Research</i> , 1990 , 161, 419-426	1.3	4
102	Optical Properties of GaSe Crystals Containing Mn Impurity Atoms. II. Excitonic and Impurity Emission. <i>Physica Status Solidi (B): Basic Research</i> , 1990 , 161, 427-434	1.3	4
101	On the possibility of the exciton-phonon bound states in GaSe. <i>Solid State Communications</i> , 1980 , 33, 621-622	1.6	4
100	Electrical and Photoelectric Properties of the TiN/p-InSe Heterojunction. <i>Semiconductors</i> , 2016 , 50, 334-338	3.8	4
99	Prompt quality monitoring of InSe and GaSe semiconductor crystals by the nuclear quadrupole resonance technique. <i>Semiconductors</i> , 2016 , 50, 1034-1037	0.7	4
98	Anomalous Low Thermal Conductivity of Atomically Thin InSe Probed by Scanning Thermal Microscopy. <i>Advanced Functional Materials</i> , 2021 , 31, 2008967	15.6	4
97	Ferroelectric semiconductor junctions based on graphene/In ₂ Se ₃ /graphene van der Waals heterostructures. <i>2D Materials</i> , 2021 , 8, 045020	5.9	4
96	Two-band conduction in electron-irradiated n-InSe single crystals. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 346-356	1.3	3
95	Effect of bremsstrahlung γ ray photons and neutrons on the parameters of indium-selenium photoconverters. <i>Semiconductors</i> , 2014 , 48, 239-244	0.7	3
94	On the photopleochroism coefficient and its temperature dynamics in native oxide-p-InSe heterojunctions. <i>Semiconductors</i> , 2014 , 48, 776-778	0.7	3
93	Temperature and baric dependence of nuclear quadruple resonance spectra in indium and gallium monoselenides 2013 ,		3
92	Fabrication and characterization of PbSe nanostructures on van der Waals surfaces of GaSe layered semiconductor crystals. <i>Nanotechnology</i> , 2015 , 26, 465601	3.4	3
91	Electrical, luminescent and photovoltaic properties of the indium tin oxide/GaSe heterojunctions with a thin layer of gallium oxide. <i>Thin Solid Films</i> , 2007 , 515, 6356-6359	2.2	3
90	A study of isotype photosensitive heterostructures (intrinsic oxide)-n-InSe prepared by long-term thermal oxidation. <i>Semiconductors</i> , 2007 , 41, 1056-1059	0.7	3
89	Experimental investigation of effect of aromatic hydrocarbons on resistivity of indium selenide. <i>Semiconductors</i> , 2007 , 41, 1197-1200	0.7	3
88	X-ray diffraction study of the molecular propolis films deposited from an alcohol solution onto the cleavage surfaces of layered V ₂ VI ₃ compounds. <i>Technical Physics</i> , 2008 , 53, 1215-1221	0.5	3

87	Characteristics of the oxide-p-InSe heterojunctions exposed to irradiation with X-ray photons. <i>Semiconductors</i> , 2006 , 40, 911-914	0.7	3
86	Optical and electrical properties of propolis films. <i>Technical Physics</i> , 2004 , 49, 1529-1530	0.5	3
85	Effect of uniaxial compression on the photoconversion parameters in a p-GaSe-n-InSe optical contact. <i>Semiconductors</i> , 2005 , 39, 600-602	0.7	3
84	Ferromagnetism of Narrow-Gap $\text{Ge}_{1-x-y}\text{Sn}_x\text{Mn}_y\text{Te}$ and Layered $\text{In}_{1-x}\text{Mn}_x\text{Se}$ Semiconductors. <i>Acta Physica Polonica A</i> , 2008 , 114, 1219-1227	0.6	3
83	Structure and magnetic properties of cobalt-intercalated layered InSe crystals. <i>Technical Physics</i> , 2014 , 59, 1462-1465	0.5	2
82	Electrochemical, optical, and magnetic properties of Ni_xInSe (0 Inorganic Materials, 2014 , 50, 976-980	0.9	2
81	Sensitive elements of pressure transducers made of layered intercalated InSe, GaSe, and Bi_2Te_3 crystals. <i>Technical Physics</i> , 2013 , 58, 1840-1843	0.5	2
80	Electrical and optical properties of Al^{3+} -intercalated InSe and GaSe. <i>Inorganic Materials</i> , 2013 , 49, 22-27	0.9	2
79	Morphology, chemical composition, and electrical characteristics of hybrid (Ni-C) nanocomposite structures grown on the van der Waals GaSe(0001) surface. <i>Physics of the Solid State</i> , 2014 , 56, 2118-2130	0.8	2
78	Effect of annealing on the spectra of nuclear quadrupole resonance in gallium-indium selenides and characteristics of structures based on these materials. <i>Semiconductors</i> , 2012 , 46, 1145-1151	0.7	2
77	Negative capacitance of native oxide films on (0001) InSe fracture surfaces. <i>Inorganic Materials</i> , 2011 , 47, 847-852	0.9	2
76	Asymmetric current flow in a native oxide/indium selenide heterostructure. <i>Inorganic Materials</i> , 2011 , 47, 1178-1182	0.9	2
75	Electrical properties of magnesium-intercalated InSe. <i>Inorganic Materials</i> , 2009 , 45, 846-850	0.9	2
74	Hydrogen Sorption in Layered Nanoporous GaSe Crystals. <i>NATO Science for Peace and Security Series C: Environmental Security</i> , 2008 , 765-777	0.3	2
73	Photosensitivity of heterojunctions formed by deposition of gum on a layered III-VI semiconductor. <i>Technical Physics</i> , 2007 , 52, 1178-1182	0.5	2
72	Electrical properties of hydrogenated InSe crystals. <i>Inorganic Materials</i> , 2006 , 42, 1308-1310	0.9	2
71	Change of built-in-potential in heterostructures induced by X-ray irradiation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006 , 246, 118-121	1.2	2
70	Mechanisms of current transfer and photosensitivity in Zn/CuInSe_2 Schottky diodes. <i>Technical Physics Letters</i> , 2006 , 32, 459-462	0.7	2

- 69 X-ray diffraction investigation of the structure of propolis films. *Physics of the Solid State*, **2006**, 48, 1602-1604 2
- 68 Surface barrier Sn-CuInSe₂ junctions. *Technical Physics Letters*, **2004**, 30, 402-403 0.7 2
- 67 The electrical and photoelectrical properties of n-In₂Se₃-p-InSe heterostructures. *Technical Physics Letters*, **2002**, 28, 711-713 0.7 2
- 66 Barrier formation in a heterostructure formed of native oxide and p-InSe. Electrical and photoelectrical properties. *Semiconductors*, **2003**, 37, 187-193 0.7 2
- 65 Semiconductor-propolis heterojunction. *Technical Physics Letters*, **2003**, 29, 867-870 0.7 2
- 64 Asymmetric current transfer in isotype n-In₂Se₃/n-InSe heterocontacts. *Technical Physics Letters*, **2005**, 31, 728 0.7 2
- 63 On a mechanism of photo-E.M.F. formation in SIS structures. *Physica Status Solidi A*, **1988**, 108, K115-K118 2
- 62 An Isothermal Annealing Effect on the Luminescence Spectra of GaSe Single Crystals. *Physica Status Solidi (B): Basic Research*, **1984**, 123, K63-K67 1.3 2
- 61 Effect of Electron Irradiation on Conductivity Anisotropy in n-InSe. *Journal of Nano- and Electronic Physics*, **2017**, 9, 06013-1-06013-5 1.5 2
- 60 Tunable spin-orbit coupling in two-dimensional InSe. *Physical Review B*, **2021**, 104, 3-3 2
- 59 Resonance and antiresonance in Raman scattering in GaSe and InSe crystals. *Scientific Reports*, **2021**, 11, 924 4.9 2
- 58 Photoelectric properties of n-ITO/p-GaTe heterojunctions. *Semiconductors*, **2015**, 49, 600-603 0.7 1
- 57 Formation of PbMn₂ alloys: Structural, photoluminescence and nuclear quadrupole resonance studies. *Journal of Alloys and Compounds*, **2020**, 824, 153985 5.7 1
- 56 Anisotropy of resistivity in Bi_{93.99}Mn₆Fe_{0.01}. *Low Temperature Physics*, **2015**, 41, 314-316 0.7 1
- 55 Structural characteristics and magnetic properties of cobalt-intercalated A₅₂B₆₃ single crystals. *Technical Physics*, **2015**, 60, 1658-1662 0.5 1
- 54 NMR Investigations of Hydrogen Intercalates in GaSe Layered Crystals. *NATO Science for Peace and Security Series C: Environmental Security*, **2011**, 443-458 0.3 1
- 53 Electric performance and photosensitivity of heterostructures prepared by thermal decomposition of a gallium nitrate aqueous solution on an indium selenide (0001) cleaved surface. *Technical Physics*, **2009**, 54, 397-401 0.5 1
- 52 Oxide films on the surface of GaSe doped with Cd or Dy. *Inorganic Materials*, **2008**, 44, 680-686 0.9 1

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